

Typical Applications

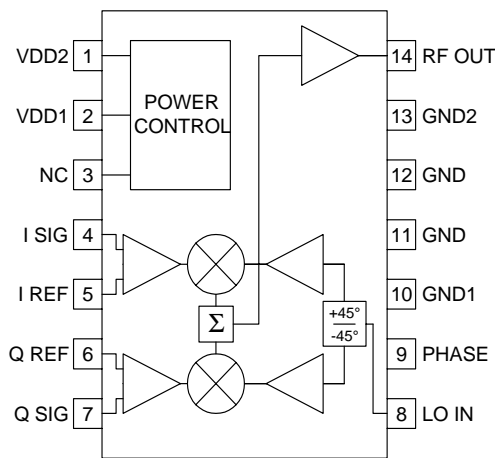
- Digital and Spread-Spectrum Systems
- GMSK, QPSK, DQPSK, QAM Modulation
- Private Mobile Radio and TETRA systems
- AM, SSB, DSB Modulation
- Image-Reject Upconverters

Product Description

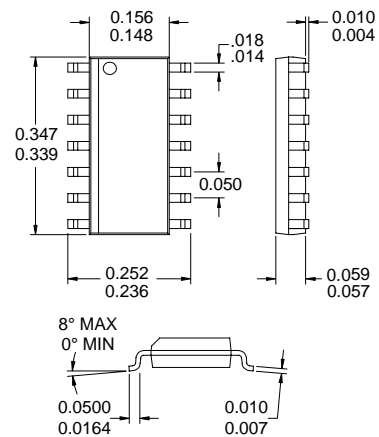
The RF2485 is a monolithic integrated universal modulation system capable of generating modulated AM, PM, or compound carriers in the VHF and UHF frequency range. The IC contains all of the required components to implement the modulation function including differential amplifiers for the baseband inputs, a 90° hybrid phase splitter, limiting LO amplifiers, two balanced mixers, a combining amplifier, and an output RF amplifier which will drive a 50Ω load. Component matching, which can only be accomplished with monolithic construction, is used to full advantage to obtain excellent amplitude balance and high phase accuracy. The unit features low power consumption, single power supply operation and adjustment free operation with no external parts required to operate the part as specified.

Optimum Technology Matching® Applied

- | | | |
|-------------------------------------|-----------------------------------|---|
| <input type="checkbox"/> Si BJT | <input type="checkbox"/> GaAs HBT | <input checked="" type="checkbox"/> GaAs MESFET |
| <input type="checkbox"/> Si Bi-CMOS | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si CMOS |



Functional Block Diagram



Package Style: SOIC-14

Features

- Single 5V Power Supply
- Low Power
- Excellent Amplitude and Phase Balance
- Extremely Low Broadband Noise Floor
- 200MHz to 600MHz Operation

Ordering Information

- | | |
|-------------|----------------------------------|
| RF2485 | VHF Quadrature Modulator |
| RF2485 PCBA | Fully Assembled Evaluation Board |

RF Micro Devices, Inc.
7625 Thorndike Road
Greensboro, NC 27409, USA

Tel (336) 664 1233
Fax (336) 664 0454
<http://www.rfmd.com>

Absolute Maximum Ratings

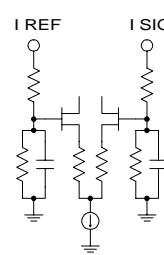
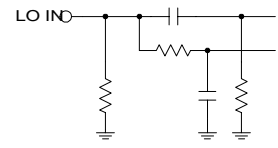
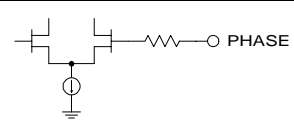
Parameter	Rating	Unit
Supply Voltage	-0.5 to +7.5	V _{DC}
Input LO and RF Levels	+10	dBm
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C



Caution! ESD sensitive device.

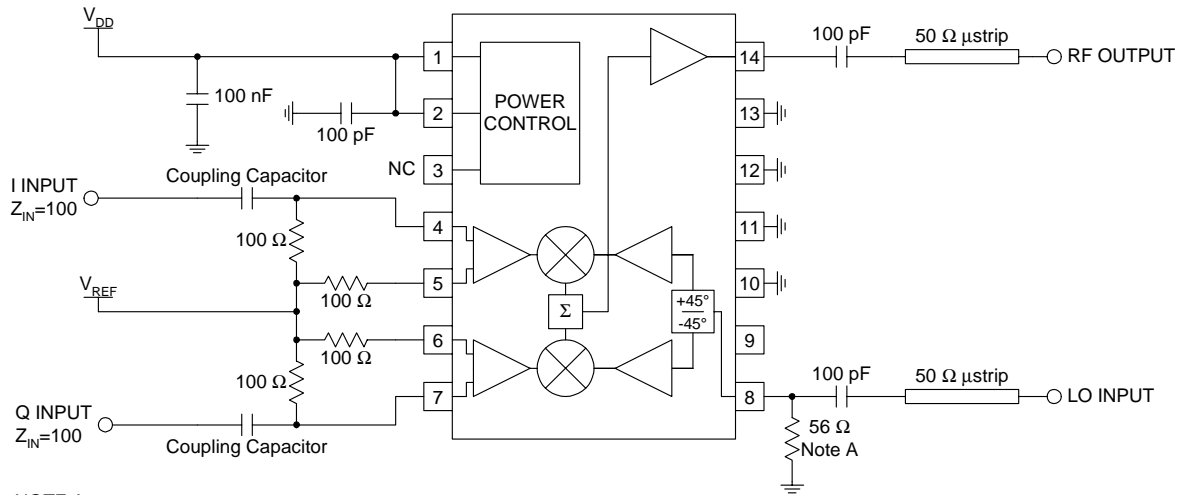
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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
LO Input					T=25°C, V _{DD} =5V _{DC} , I&Q inputs=2V _{PP}
Frequency Range	200		600	MHz	With external 50Ω termination; see application schematic, note A.
Power Level	-3		+6	dBm	
Input VSWR		1.2:1			
Modulation Input					
Frequency Range	DC		100	MHz	I & Q signals for -0.5dBm output power. I & Q signals for +5dBm output power. In-phase and quadrature signals.
Reference Voltage (V _{REF})	2.0		3.0	V	
Modulation (I&Q)		V _{REF} ±0.7		V	
Modulation (I&Q)		V _{REF} ±1.5		V	
Maximum Modulation (I&Q)		V _{REF} ±2.5		V	
Input Resistance		3000		Ω	
DC Offset		50	150	mV	
Amplitude Error (I/Q)		0.2		dB	I _{SIG} -I _{REF} and Q _{SIG} -Q _{REF} ; to achieve maximum carrier suppression.
Quadrature Phase Error		±1	±3	°	
RF Output					V _{DD} =5V, LO Power=0dBm, LO Freq=400MHz, SSB, I&Q input=0.7V _P
Output Power	-1.5	-0.5		dBm	At 5MHz offset Unadjusted Modulation DC offset can be externally adjusted for optimum suppression. Suppression is typically better than 25dB without adjustment.
Output Impedance		50		Ω	
Output VSWR		1.5:1			
Broadband Noise Floor		-149	-147	dBm/Hz	
Sideband Suppression	30	43		dB	
Carrier Suppression	20	26		dB	
IM3	-40	-52		dBc	
TETRA Modulation					1.7V _{P-P} TETRA Modulation LO, 450MHz @ -5.0dBm, V _{REF} 2.5V VCC=5.0V
Channel Power	-3.0	-2.5	-2.0	dBm	
Adjacent Channel Power Rejection				dBc	
25kHz	-47.0	-48.0	-49.0	dBc	
50kHz	-67.0	-68.5	-70.0	dBc	
Power Supply					
Voltage		5		V	Specifications
	4.5		5.5	V	Operating Limits
Current		28	39	mA	Operating

Pin	Function	Description	Interface Schematic
1	VDD2	Power supply for the RF Output amplifier. An external RF bypass capacitor is needed. The trace length between the pin and the bypass capacitor should be minimized. The ground side of the capacitor should connect immediately to the ground plane.	
2	VDD1	Power supply for all other circuits. An external RF bypass capacitor is needed.	
3	NC	No connection.	
4	I SIG	Baseband input to the I mixer. This pin is DC coupled. Maximum output power is obtained when the input signal has a peak to peak amplitude of 5V. The DC level supplied to this pin should be $2.5 \pm 0.5V$. The SIG and REF inputs are inputs of a differential amplifier. Therefore the REF and SIG inputs are interchangeable. If swapping the I SIG and I REF pins, the Q SIG and Q REF also need to be swapped to maintain the correct phase. It is also possible to drive the SIG and REF inputs in a balanced mode. This will increase the gain.	
5	I REF	Reference voltage for the I mixer. This voltage should be the same as the DC voltage supplied to the I SIG pin. To obtain a carrier suppression of better than 40dB it may be tuned $\pm 0.15V$ (relative to the I SIG DC voltage). Without tuning, it will typically be better than 25dB.	See pin 4.
6	Q REF	Reference voltage for the Q mixer. This voltage should be the same as the DC voltage supplied to the Q SIG pin. To obtain a carrier suppression of better than 40dB it may be tuned $\pm 0.15V$ (relative to the Q SIG DC voltage). Without tuning, it will typically be better than 25dB. The SIG and REF inputs are inputs of a differential amplifier. Therefore the REF and SIG inputs are interchangeable. If swapping the I SIG and I REF pins, Q SIG and Q REF also need to be swapped to maintain correct phase. It is also possible to drive the SIG and REF inputs in a balanced mode. This will increase the gain.	Same as pin 3.
7	Q SIG	Baseband input to the Q mixer. This pin is DC coupled. Maximum output power is obtained when the input signal has a peak to peak amplitude of 5V. The DC level supplied to this pin should be $2.5 \pm 0.5V$.	Same as pin 4.
8	LO IN	The input of the phase shifting network. This high impedance input can be matched with an external 56Ω termination resistor. This pin is internally connected to ground through a $4k\Omega$ resistor. Putting a DC voltage on this pin is not recommended. However, connecting this pin to ground, e.g., through a shunt inductor, is allowed.	
9	PHASE	This pin allows to adjust the phase of the I/Q signals. However, the control is very sensitive and hard to control. Control voltage change for a few degrees adjustment is in the order of 10mV. Device to device and temperature variation are not characterized. Therefore it is not recommended to use this pin; leave it not connected. Do NOT connect to ground. For compensating large errors in the I/Q signals supplied to the device or in control loops this pin may prove useful.	
10	GND1	Ground connection of the LO phase shift network. This pin should be connected directly to the ground plane.	
11	GND	Ground connection for other circuits. Keep traces short and connect to ground plane immediately.	
12	GND	Same as pin 11.	
13	GND2	Ground connection for the RF output stage. A good ground connection is especially important at this pin to avoid interference with other circuits.	

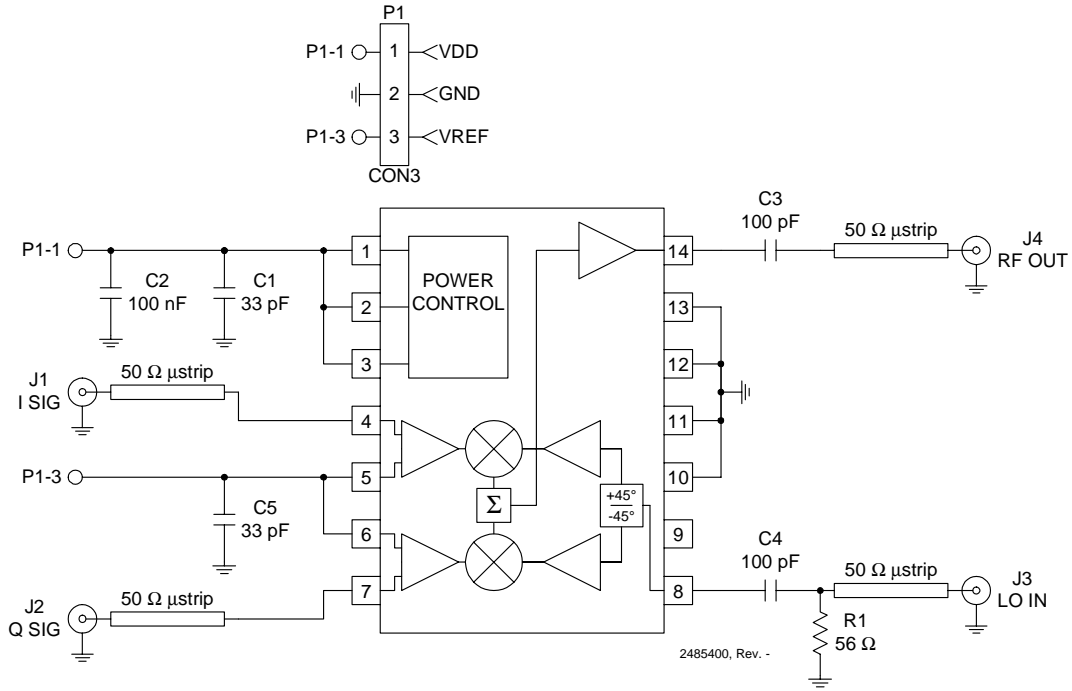
Pin	Function	Description	Interface Schematic
14	RF OUT	50Ω output. This pin carries a DC voltage, and an external blocking capacitor is recommended.	

Application Schematic



NOTE A: Optional; input impedance is about 79-J158 Ω at 400 MHz without resistor. SMD resistor mounted adjacent to package pin, grounded through a via to the ground plane.

Evaluation Board Schematic (Download [Bill of Materials](http://www.rfmd.com) from www.rfmd.com.)



Evaluation Board Layout
Board Size 2.0" x 2.0"
Board Thickness 0.031", Board Material FR-4

